

**CITY UNIVERSITY OF HONG KONG**

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Studying the Effect of Carbon Substrates on Cubic Boron Nitride  
Film Growth

立方氮化硼膜生長於碳基底的研究

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## Abstract

Cubic BN (cBN) is the material with the second highest hardness, elastic modulus and thermal conductivity next to diamond. It is, however, superior to diamond in higher graphitization and oxidation temperatures and chemical inertness to molten ferrous materials. These properties make cBN the best material for mechanical applications involving steels and all ferrous materials. Cubic BN is also a potential candidate for construction of high-power and high-speed electronic devices owing to its high thermal conductivity and electronic properties. It has a wide bandgap (~6.2 eV), high carrier mobility and doping capacity for both n- and p-type conductivity, while n-type doping of competitive diamond is still questionable. The wide bandgap characteristic makes cBN suitable for ultraviolet (UV) detectors and UV light emitting diodes (LEDs). The extreme properties also make cBN films very attractive for space and nuclear fusion applications.

Many types of substrates have been used at cBN synthesis, but because of the mismatch of physical and chemical parameters of the substrate and cBN as well as their compatibility, many cBN syntheses have had very poor outputs. Cubic BN films often grow via an intermediate amorphous/turbostratic (aBN/tBN) layer on many substrates. The energetic ion bombardment essential for cBN formation and the existence of soft and humidity sensitive aBN/tBN precursor layers lead to high compressive stress, poor film adhesion and stability as well as limited film thickness (<200 nm) and thus hamper practical applications.

This research work studies the effect of carbon substrates on cBN film growth and provides evidences that carbon substrates are generally suitable for cBN growth particularly because of carbon chemical nature. Carbon systems are compatible with BN systems and can be used in many cases of cBN deposition as interlayer to enhance adhesion and functionality of the films. The carbon substrates employed in this study

are amorphous tetrahedral carbon (ta-C) and nanocrystalline diamond (nanodiamond) films deposited on silicon substrates.

Introducing ta-C as interlayers enables deposition of more adherent cBN films with higher cubic phase content and better crystalline quality than those prepared on bare Si substrates. The partial transformation of ta-C interlayers at high deposition temperature (~900 °C) with the effect of ion bombardment results in some graphitic carbon structures with basal planes preferentially oriented perpendicular to the substrates. High-resolution transmission electron microscopy (HRTEM) combining with elemental mappings using electron energy loss spectroscopy (EELS) show that oriented tBN grows directly on the restructured carbon interlayer without intermediate amorphous BN layer. The cBN films grown on these interlayers are stable in ambient environment. The film stability is provided by carbon atoms in the interfacial zones. Carbon atoms diffuse and passivate the reactive boron-dangling bonds at BN/C interface. The thermally driven carbon diffusion is enhanced by unceasing ion bombardment. The dense  $sp^3$ -bonded carbon structure at the interface in addition confines the residual reactive boron sites and acts as a barrier obstructing water and oxygen diffusion into these sites. Thus, it precludes oxidation reaction and formation of unstable boron oxide and oxyhydrides that otherwise would lead to film delamination. The restructured carbon interlayer also improves the crystallinity of the oriented tBN layer because of their similar structure which consequently results in reducing the nitrogen-void defects and enhancing the film stability.

The effect of nanodiamond buffer layer on the nucleation and growth of cBN film is studied based on detailed HRTEM analyses. The direct growth of cBN on nanodiamond crystals without aBN/tBN interfacial layers is found owing to the similarity in lattice parameters and physical properties of cBN and diamond as well as nanocrystalline nature of both materials. Some cBN crystals grow on diamond nanocrystals with twinning orientation. Epitaxial relation of  $(111)_{\text{cBN}}$  parallel to  $(111)_{\text{Diamond}}$  planes is observed as well as small-angle cBN/diamond grain boundaries

of about 5-6 degrees because of the slight lattice mismatch. It is also found in some local areas that oriented tBN nucleates on amorphous carbon region serving as cBN nucleation sites. The cBN and surface layers are well crystallized without notable hBN/tBN inclusions. Cubic BN nanocrystals seem to extend directly to the film surface while tBN/aBN structures covering the cBN crystals are hardly observed. The reason is attributed to the considerable reduction of ion kinetic energy during film growth.

The phase composition and crystallinity of cBN films were also been are usually investigated by spectroscopic methods, such as visible Raman and Fourier transform infrared (FTIR) spectroscopy. However, cBN signal in visible Raman analysis does not usually emerge when the structure is nanocrystalline and highly defective, especially for films prepared by physical vapor deposition (PVD). In this research work, cBN films grown on nanodiamond by radio-frequency magnetron sputtering (RF-MS) at record low bias voltage (-35 V) among PVD methods are investigated by ultraviolet (UV) Raman spectroscopy. The UV Raman spectroscopy is obviously more powerful for hBN identification in contrast to FTIR analysis owing to a very large scattering cross-section of hBN structure at UV light excitation. In comparison to FTIR spectroscopy, UV Raman scattering is demonstrated herein to identify the crystalline quality of thick cBN films. It also enables the quantitative estimation of cBN content of thick cBN films contrasting the FTIR analysis which is influenced by the interfacial structure and film thickness.

The mechanical properties of cBN/nanodiamond multilayer coatings are investigated by nanoindentation measurements and compared with those of individual cBN and nanodiamond layers. The residual stresses are estimated using an optical interference method. The deposition time of each layer was well controlled in order to obtain equivalent thicknesses (~100 nm) of all consecutive layers. Engineering the cBN/nanodiamond multilayer enhances the properties of individual materials and introduces novel properties of the multilayer coating. The much lower stress confined

in multilayer film as compared with single-layered cBN film extends the interest for using cBN/nanodiamond multilayer films in cutting tools and tribological applications.

Briefly the major and pioneering contributions of this work to the presented field are:

- i) Synthesis of thick films ( $>1 \mu\text{m}$ ) on carbon substrates. Limitation is particularly in deposition rate which can significantly be increased by scaling up the system and deposition power used.
- ii) Record low bias voltage ( $-35 \text{ V}$ ) ever applied for PVD growth yielding cBN films.
- iii) Considerably improved crystallinity of cBN films prepared by PVD method.
- iv) Original study of the role of carbon at passivation of boron-dangling bonds for preparation of thick and stable cBN films.
- v) First study and detection of traces of hBN in cBN films, which are below the detection limit of conventional FTIR technique, using UV Raman spectroscopy.
- vi) Design and fabrication of the first cBN/nanodiamond super-lattices with extreme mechanical properties (hardness of 82 GPa) and exceptional smooth surface morphologies (roughness of 9.8 nm).

## Table of contents

<b>Abstract.....</b>	<b>i</b>
<b>Acknowledgements.....</b>	<b>v</b>
<b>Table of contents.....</b>	<b>vi</b>
<b>List of figures.....</b>	<b>viii</b>
<b>List of tables.....</b>	<b>xii</b>
<b>Chapter 1 Structures and properties of boron nitride polymorphs.....</b>	<b>1</b>
1.1 Crystalline and non-crystalline structures of boron nitride.....	2
1.2 Identification of BN phases via vibrational modes.....	5
1.3 Extreme properties of cBN leading to mechanical applications.....	7
1.4 Electronic and electrical properties of cBN.....	10
<b>Chapter 2 Phase diagram of boron nitride.....</b>	<b>13</b>
<b>Chapter 3 Mechanistic models of cBN film formation with ion assistance..</b>	<b>15</b>
3.1 Ion-related parameters controlling cBN film growth.....	15
3.2 Sputter model.....	17
3.3 Thermal-spike quenching.....	18
3.4 Stress-induced cBN formation.....	19
3.5 Subplantation model.....	20
3.6 Surface growth.....	21
3.7 Summary to growth mechanism.....	22
<b>Chapter 4 Synthesis of cBN films by physical vapor deposition.....</b>	<b>23</b>
4.1 Control of film stress and adhesion in PVD.....	23
4.2 Obtaining thick films through interfacial design.....	25
4.3 Remarks to PVD synthesis of cBN.....	27
<b>Chapter 5 Synthesis of cBN using plasma enhanced chemical vapor deposition.....</b>	<b>28</b>
5.1 Remarkable achievement in cBN synthesis by fluorine chemistry.....	28
5.2 Route to practical application with the aid of electron cyclotron resonance..	30
5.3 Summary of cBN synthesis by PECVD.....	32
<b>Chapter 6 Experimental methods and characterization techniques employed.....</b>	<b>34</b>
6.1 Deposition system used in BN synthesis.....	34
6.2 Analysis of BN films by various characterization techniques.....	36

<b>Chapter 7 Deposition of cBN on amorphous tetrahedral carbon interlayers.....</b>	<b>38</b>
7.1 Briefing on motivation and deposition conditions.....	38
7.2 Comparison of substrate in deposition of cBN.....	40
7.3 Investigation of structural change of ta-C at high temperature.....	44
7.4 Effect of restructured ta-C interfacial layer on the nucleation of cBN.....	47
7.5 Role of restructured ta-C on the enhancement of cBN film adhesion.....	49
7.6 Summary of growing cBN on ta-C.....	53
<b>Chapter 8 Spectroscopic study of cBN films.....</b>	<b>55</b>
8.1 Growth of cBN films at record low substrate bias voltage.....	56
8.2 Spectroscopic and morphological analyses of cBN films.....	59
8.3 FTIR and UV Raman qualitative analyses of thick cBN films in constrast...	66
8.4 Significance of spectroscopic analysis of cBN films.....	69
<b>Chapter 9 Nucleation and growth of cBN on nanodiamond buffer layers... </b>	<b>70</b>
9.1 Characteristic growth pattern of cBN.....	70
9.2 Examination of the nanodiamond/Si substrate for cBN growth.....	72
9.3 Atomic scale investigation of cBN/nanodiamond interface.....	74
9.4 Surface of cBN films.....	80
9.5 Summary to the growth of cBN on nanodiamond.....	85
<b>Chapter 10 cBN/nanodiamond multilayer coatings.....</b>	<b>86</b>
10.1 Inspiration and experience in deposition of multilayered systems.....	86
10.2 Stress and mechanical measurements on cBN/nanodiamond multilayers....	89
10.3 Final remarks of cBN/nanodiamond multilayer film.....	97
<b>Chapter 11 Conclusions.....</b>	<b>98</b>
<b>References.....</b>	<b>101</b>
<b>List of publications.....</b>	<b>107</b>
<b>Abstract of publications.....</b>	<b>110</b>

## List of figures

- Fig. 1-1 Crystal structures of hBN, wBN, rBN and cBN. The unit cells of the four BN modifications are indicated by red dotted lines.
- Fig. 1-2 Identification of BN phases using vibrational spectroscopies. (a) Visible Raman spectrum of hBN, (b) FTIR spectrum of hBN film, (c) visible Raman spectrum of cBN synthesized by HPHT method and (d) FTIR spectrum of cBN film grown on Si substrate.
- Fig. 2-1 Fig. 2-1. Phase  $p,T$ -diagram of boron nitride (solid lines, refined diagram; dashed lines, Solozhenko's diagram [62]). Solid squares show Wentorf's data on hBN melting [63]. Solid circle is the melting point of cBN at 10 GPa [64] and solid triangle is hBN melting point at 50 MPa [65]. From Solozhenko et al. [60].
- Fig. 3-1 Schematic diagram indicating the region of cBN film formation as a function of ion current and ion energy. From Inagawa et al. [66].
- Fig. 3-2 Schematic representation of the stress model of cBN formation.
- Fig. 6-1 A schematic drawing of RF-MS deposition system employed in the synthesis of BN films.
- Fig. 7-1 FTIR spectra of BN films deposited on (a) bare Si and (b) ta-C coated substrates at  $\sim 870$  °C for 3 h at different bias voltages.
- Fig. 7-2 Contents of cubic phase in BN films deposited on bare Si and ta-C coated substrates differ upon the bias voltage used.
- Fig. 7-3 FTIR spectra showing cBN evolution on bare Si and ta-C coated substrates at -65 V and  $\sim 870$  °C illustrated with deposition time of 1 – 3 h.
- Fig. 7-4 Normalized visible Raman spectra collected from a ta-C film as-deposited on Si substrate (ta-C/Si) and a restructured ta-C film during BN deposition at  $\sim 870$  °C; second-order silicon peak is at  $970\text{ cm}^{-1}$  while BN is not identified because of its nanocrystalline nature.
- Fig. 7-5 Cross-sectional HRTEM image taken at the restructured ta-C/Si interface. The inset represents FT of the image. In the upper region, the restructured carbon interlayer shows its (0002) graphite planes favorably aligned in the perpendicular direction to the (200) plane of Si



substrate as evidenced by FT of the image.

- Fig. 7-6 (a) Cross-sectional HRTEM image of the tBN/restructured ta-C interface. Oriented tBN grows directly on restructured ta-C without aBN interface; (b) boron and (c) carbon elemental mapping indicating the BN/carbon interface.
- Fig. 7-7 Cross-sectional HRTEM image taken at the cBN/tBN interface. The cBN growth was on a ta-C coated Si substrate.
- Fig. 7-8 Graphical illustration of terminating boron-dangling bonds by carbon atoms.
- Fig. 7-9 SEM image showing the cross section of a cBN film with thickness of ~350 nm grown on a restructured ta-C interlayer. The inset is the corresponding FTIR spectrum with a narrow cBN TO absorption peak.
- Fig. 8-1 FTIR spectra of BN films grown on nanodiamond at different bias voltages.
- Fig. 8-2 FTIR spectrum of a 30-nm-thick cBN film deposited on nanodiamond coated Si substrate at bias voltage of -60 V.
- Fig. 8-3 Visible Raman spectra of uncoated nanodiamond before and after cBN deposition at bias voltage of -35 V.
- Fig. 8-4 Cross-sectional SEM images of cBN films with thickness of (a) 480, (b) 780 and (c) 1.1  $\mu\text{m}$ .
- Fig. 8-5 (a) FTIR and (b) UV Raman spectra of cBN films of different thicknesses grown on nanodiamond at -35 V. The Raman spectrum of an uncoated nanodiamond film is cited as a reference in (b).
- Fig. 8-6 UV Raman spectra of cBN films with the same thickness of ~250 nm grown at -35 and -60 V, respectively. The inset shows their corresponding FTIR spectra.
- Fig. 8-7 SEM surface images of cBN films grown at -35 and -60 V, respectively. The images are taken at identical conditions and parameters of electron beam.
- Fig. 9-1 Cross-sectional HRTEM image of the interfacial cBN-tBN region. Note the cBN is nucleated on the edges of textured tBN (0002) planes.

- Fig. 9-2 Cross-sectional HRTEM images showing (a) the nanodiamond layer and (b) the nanodiamond/Si interface.
- Fig. 9-3 (a) Cross-sectional bright field TEM image taken at cBN/nanodiamond interface; (b) The boundary between cBN and nanodiamond is revealed by elemental mapping of boron using EELS.
- Fig. 9-4 FTIR spectrum acquired from the BN film grown on nanodiamond film prepared on Si substrate. The spectrum indicates a nearly pure cBN structure.
- Fig. 9-5 Cross-sectional HRTEM images of the cBN/nanodiamond interface: (a) Epitaxial growth of cBN nanocrystals on nanodiamond without aBN/tBN layer; (b) Direct growth of cBN on nanodiamond with twinning orientation relation. White arrows indicate the interfacial region.
- Fig. 9-6 Cross-sectional HRTEM images taken at the cBN/nanodiamond interface showing epitaxial growth of cBN on diamond with small-angle grain boundary (region inside the black rectangle) and extension of tBN from amorphous carbon region. Note that the interface is denoted by arrows.
- Fig. 9-7 HRTEM image showing the structure cBN film grown on nanodiamond buffer layer at  $-35$  V and  $900$  °C.
- Fig. 9-8 Cross-sectional HRTEM image at the near-surface region of the cBN film. The FT image inserted corresponds to the framed area. Spots corresponding to  $(111)_{\text{cBN}}$  planes are marked by circles in the inset.
- Fig. 10-1. FTIR spectra of (a) cBN/nanodiamond multilayer and (b) cBN single layer. The corresponding Newton-ring patterns are shown in the insets. The coatings are both  $500$  nm in thickness and grown on a  $2.5\text{-}\mu\text{m}$ -thick nanodiamond buffer layer.
- Fig. 10-2. Cross-sectional SEM micrograph showing the cBN/nanodiamond multilayer film grown on nanodiamond (ND) buffer layer. (a) An overall view and (b) an enlarged view SEM image revealing five layers with rather uniform thickness.
- Fig. 10-3. AFM topographical image of cBN/nanodiamond multilayer film collected at scan size of  $5 \times 5 \mu\text{m}^2$ .

- Fig. 10-4. Hardness values of nanodiamond buffer layer, cBN single layer and cBN/nanodiamond multilayer determined from nanoindentation measurements in the plain-view direction.
- Fig. 10-5. Hardness and elastic modulus of a 0.9- $\mu\text{m}$ -thick cBN/nanodiamond multilayer film with nine layers. Inset shows the cross-sectional SEM micrograph of the film.

**List of tables**

- Table 1-1 Comparison of some properties of diamond and cBN.
- Table 6-1 Process parameters for the deposition of BN films by RF-MS.
- Table 6-2 Characterization techniques used in this study.
- Table 8-1 The fundamental deposition parameters for the synthesis of BN films with higher cBN content than 85 % by sputtering process.